

Y-J Cho

List of Publications by Year in descending order

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45
papers

1,203
citations

430754

18
h-index

377752

34
g-index

45
all docs

45
docs citations

45
times ranked

1770
citing authors

#	ARTICLE	IF	CITATIONS
1	Valence-band anticrossing in mismatched III-V semiconductor alloys. <i>Physical Review B</i> , 2007, 75, .	1.1	354
2	Deep ultraviolet emission in hexagonal boron nitride grown by high-temperature molecular beam epitaxy. <i>2D Materials</i> , 2017, 4, 021023.	2.0	102
3	Crystal orientation dictated epitaxy of ultrawide-bandgap 5.4- to 8.6-eV $\text{In}_{1-x}\text{Al}_x\text{N}$ on m-plane sapphire. <i>Science Advances</i> , 2021, 7, .	4.7	71
4	The new nitrides: layered, ferroelectric, magnetic, metallic and superconducting nitrides to boost the GaN photonics and electronics eco-system. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SC0801.	0.8	69
5	Hexagonal Boron Nitride Tunnel Barriers Grown on Graphite by High Temperature Molecular Beam Epitaxy. <i>Scientific Reports</i> , 2016, 6, 34474.	1.6	60
6	Strain-Engineered Graphene Grown on Hexagonal Boron Nitride by Molecular Beam Epitaxy. <i>Scientific Reports</i> , 2016, 6, 22440.	1.6	49
7	Integrated nano-opto-electro-mechanical sensor for spectrometry and nanometrology. <i>Nature Communications</i> , 2017, 8, 2216.	5.8	41
8	Near-bandgap wavelength dependence of long-lived traveling coherent longitudinal acoustic phonons in GaSb-GaAs heterostructures. <i>Physical Review B</i> , 2006, 74, .	1.1	38
9	Dynamically controlling the emission of single excitons in photonic crystal cavities. <i>Nature Communications</i> , 2014, 5, 5786.	5.8	31
10	Thermal stability of epitaxial $\text{In}_x\text{Ga}_{1-x}\text{N}$ and $(\text{Al,Ga})\text{N}$ layers on m-plane sapphire. <i>Applied Physics Letters</i> , 2021, 119, .	1.5	30
11	Molecular beam homoepitaxy on bulk AlN enabled by aluminum-assisted surface cleaning. <i>Applied Physics Letters</i> , 2020, 116, .	1.5	26
12	Surface control and MBE growth diagram for homoepitaxy on single-crystal AlN substrates. <i>Applied Physics Letters</i> , 2020, 116, .	1.5	26
13	Rotationally aligned hexagonal boron nitride on sapphire by high-temperature molecular beam epitaxy. <i>Physical Review Materials</i> , 2019, 3, .	0.9	25
14	High temperature MBE of graphene on sapphire and hexagonal boron nitride flakes on sapphire. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016, 34, .	0.6	22
15	Investigation of magnetic and electronic coupling between two $(\text{Ga,Mn})\text{As}$ layers in $(\text{Ga,Mn})\text{As}/\text{GaAs}/(\text{Ga,Mn})\text{As}$ magnetic tunnel junctions. <i>Applied Physics Letters</i> , 2007, 91, 152109.	1.5	20
16	Structural properties of InN films grown on O-face ZnO(0001) by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2012, 100, 152105.	1.5	20
17	Effects of donor doping on $\text{Ga}_{1-x}\text{Mn}_x\text{As}$. <i>Applied Physics Letters</i> , 2008, 93, .	1.5	19
18	Anisotropic dielectric functions, band-to-band transitions, and critical points in $\text{In}_x\text{Ga}_{1-x}\text{N}$ on $\text{AlN}/\text{Ga}_2\text{O}_3$. <i>Applied Physics Letters</i> , 2021, 118, .	1.5	19

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19	Growth of wurtzite InN on bulk In ₂ O ₃ (111) wafers. Applied Physics Letters, 2012, 101, .	1.5	16
20	Polarization-induced 2D hole gases in pseudomorphic undoped GaN/AlN heterostructures on single-crystal AlN substrates. Applied Physics Letters, 2021, 119, .	1.5	15
21	Auger recombination as the dominant nonradiative recombination channel in InN. Physical Review B, 2013, 87, .	1.1	14
22	Single-crystal N-polar GaN $\langle 100 \rangle$ diodes by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2017, 110, .	1.5	14
23	High-frequency and below bandgap anisotropic dielectric constants in $\langle 100 \rangle$ -Al _x Ga _{1-x} N ₂ O ₃ (x=0.1). Applied Physics Letters, 2021, 119, .	1.5	14
24	N-polar GaN/AlN resonant tunneling diodes. Applied Physics Letters, 2020, 117, .	1.5	12
25	Pump-probe studies of travelling coherent longitudinal acoustic phonon oscillations in GaAs. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2632-2636. Infrared dielectric functions and Brillouin zone center phonons of $\langle 100 \rangle$ -Al _x Ga _{1-x} N ₂ O ₃ (x=0.1) compared to $\langle 100 \rangle$ -Al _x Ga _{1-x} N ₂ O ₃ (x=0.1). Physical Review Materials, 2021, 5, 014401.	0.8	11
26	Raman scattering by wave-vector-dependent coupled plasmon/LO-phonon modes in $\langle 100 \rangle$ -Al _x Ga _{1-x} N ₂ O ₃ (x=0.1) type InN. Physical Review B, 2012, 85, .	0.9	10
27	High-mobility two-dimensional electron gases at AlGa _x N/GaN heterostructures grown on GaN bulk wafers and GaN template substrates. Applied Physics Express, 2019, 12, 121003.	1.1	9
28	Blue (In,Ga)N light-emitting diodes with buried $\langle 100 \rangle$ tunnel junctions by plasma-assisted molecular beam epitaxy. Japanese Journal of Applied Physics, 2019, 58, 060914.	0.8	6
29	Magnetic properties of MBE grown Mn ₄ N on MgO, SiC, GaN and Al ₂ O ₃ substrates. AIP Advances, 2020, 10, .	0.6	6
30	Observation of the electron-accumulation layer at the surface of InN by cross-sectional micro-Raman spectroscopy. Applied Physics Letters, 2013, 102, .	1.5	5
31	In-assisted deoxidation of GaAs substrates for the growth of single InAs/GaAs quantum dot emitters. Semiconductor Science and Technology, 2015, 30, 055009.	1.0	5
32	Impact of substrate nitridation on the growth of InN on In ₂ O ₃ (111) by plasma-assisted molecular beam epitaxy. Applied Surface Science, 2016, 369, 159-162.	3.1	5
33	Characteristics of three-beam photoreflectance in ZnTe/GaAs with deep traps. Solid State Communications, 1999, 110, 605-609.	0.9	4
34	Collapse of ferromagnetism in (Ga, Mn)As at high hole concentrations. Semiconductor Science and Technology, 2008, 23, 125010.	1.0	4
35	Infrared-active phonon modes and static dielectric constants in $\langle 100 \rangle$ -Al _x Ga _{1-x} N ₂ O ₃ (0.18 ≤ x ≤ 0.54) alloys. Applied Physics Letters, 2022, 120, .	1.5	4

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37	N-polar GaN p-n junction diodes with low ideality factors. Applied Physics Express, 2022, 15, 064004.	1.1	4
38	Valence band anticrossing in mismatched III-V semiconductor alloys. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 1711-1714.	0.8	3
39	Magnetic anisotropy of ferromagnetic Ga _{1-x} Mn _x As formed by Mn ion implantation and pulsed-laser melting. Journal of Applied Physics, 2008, 104, 043902.	1.1	3
40	Epitaxial Ferrimagnetic Mn ₄ N Thin Films on GaN by Molecular Beam Epitaxy. IEEE Transactions on Magnetics, 2022, 58, 1-6.	1.2	3
41	Effects of Ga on the growth of InN on O-face ZnO(0001 \hat{A}) by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2012, 101, 052103.	1.5	2
42	Magnetic cluster phases of Mn-interstitial-free (Ga,Mn)As. AIP Conference Proceedings, 2007, , .	0.3	1
43	Vanishing of ferromagnetic order in (Ga,Mn)As films at high hole concentrations: beyond the mean field Zener model. Journal of Applied Physics, 2008, 103, 07D132.	1.1	1
44	GaN/AlGa _n 2DEGs in the quantum regime: Magneto-transport and photoluminescence to 60 tesla. Applied Physics Letters, 2020, 117, 262105.	1.5	1
45	Integrated spectrometer and displacement sensor based on mechanically tunable photonic crystals. , 2017, , .		0